Surface Mount Schottky Power Rectifier

This device employs the Schottky Barrier principle in a large area metal-to-silicon power diode. State-of-the-art geometry features epitaxial construction with oxide passivation and metal overlay contact. Ideally suited for low voltage, high frequency rectification, or as free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system.

Features

- Low Profile Package for Space Constrained Applications
- Rectangular Package for Automated Handling
- Highly Stable Oxide Passivated Junction
- 150°C Operating Junction Temperature
- Guard-Ring for Stress Protection
- NRV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free and Halide-Free Devices

Mechanical Charactersistics

- Case: Epoxy, Molded, Epoxy Meets UL 94, V-0
- Weight: 95 mg (approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C Max. for 10 Seconds
- Cathode Polarity Band
- Device Meets MSL 1 Requirements



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SCHOTTKY BARRIER RECTIFIER 4.0 AMPERE 40 VOLTS



SMA-FL CASE 403AA STYLE 6

MARKING DIAGRAM



RAF = Specific Device Code A = Assembly Location

= Year

WW = Work Week ■ Pb–Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
MBRAF440T3G	SMA-FL (Pb-Free)	5000 / Tape & Reel
NRVBAF440T3G	SMA-FL (Pb-Free)	5000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	40	V
Average Rectified Forward Current (At Rated V _R , T _L = 107°C)		lo	4.0	А
Non-Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Sing	e Phase, 60 Hz)	I _{FSM}	100	А
Storage/Operating Case Temperature		T _{stg} , T _C	-55 to +150	°C
Operating Junction Temperature (Note 1)		TJ	-55 to +150	°C
Voltage Rate of Change (Rated V _R , T _J = 25°C)		dv/dt	10,000	V/μs
ESD Rating	Human Body Model Machine Model	ESD _{HBM} ESD _{MM}	3B M4	-

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction–to–Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance – Junction–to–Lead (Note 2) Thermal Resistance – Junction–to–Ambient (Note 2)	R _{θJL} R _{θJA}	25 90	°C/W

^{2. 1} inch square pad size (1 \times 0.5 inch) for each lead on FR4 board.

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Va	lue	Unit
Maximum Instantaneous Forward Voltage (Note 3)	V _F	T _J = 25°C	T _J = 100°C	V
$(I_F = 4.0 \text{ A})$		0.485	0.435	
Maximum Instantaneous Reverse Current	I _R	T _J = 25°C	T _J = 100°C	mA
$(V_R = 40 \text{ V})$		0.3	15	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{3.} Pulse Test: Pulse Width \leq 250 μ s, Duty Cycle \leq 2.0%.

TYPICAL CHARACTERISTICS

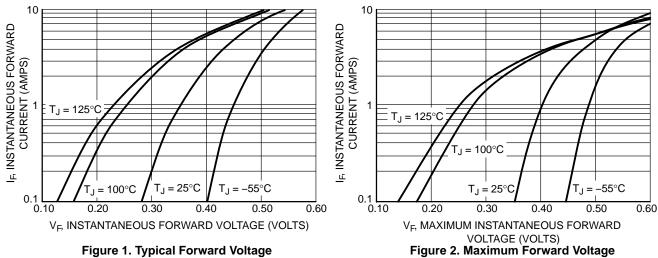


Figure 1. Typical Forward Voltage

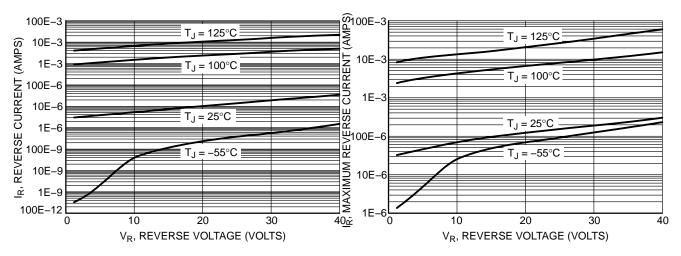


Figure 3. Typical Reverse Current

SQUARE

WAVE

 $I_{pk}/I_{O} = 5$

 $I_{pk}/I_O = 10$

3.5

3

dc

 $I_{pk}/I_O = \pi$

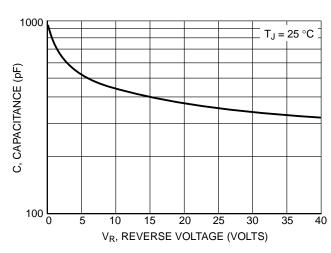


Figure 4. Maximum Reverse Current

IO, AVERAGE FORWARD CURRENT (AMPS) **Figure 5. Forward Power Dissipation**

2.5

 $I_{pk}/I_O = 20$

P_{FO}, AVERAGE POWER DISSIPATION (WATTS)

1.8

1.6

1.4

1.2 1.0 0.8

0.6

0.4

0.2

Figure 6. Capacitance

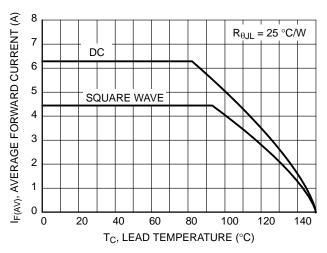


Figure 7. Current Derating

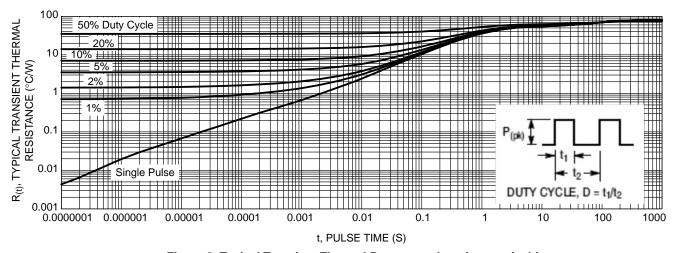
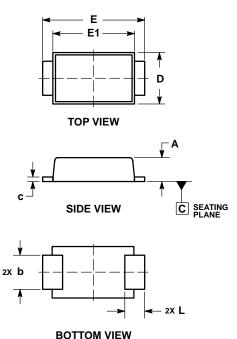


Figure 8. Typical Transient Thermal Response, Junction-to-Ambient

PACKAGE DIMENSIONS

SMA-FL CASE 403AA ISSUE A

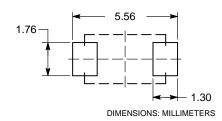


NOTES:

- DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M. 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS.

	MILLIMETERS		
DIM	MIN MAX		
Α	0.90	1.10	
b	1.25	1.65	
С	0.15	0.30	
D	2.40	2.80	
Е	4.80	5.40	
E1	4.00	4.60	
L	0.70	1.10	

RECOMMENDED SOLDER FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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